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Patent Assignment Abstract of Title

Total Assignments: 2

Application #: 09184490   **Filing Dt:** 11/02/1998   **Patent #:** 6325858   **Issue Dt:** 12/04/2001

PCT #: NONE   **Publicati n #:** NONE   **Pub Dt:**

Inventors: JOHN F. WENGERT, IVO RAAIJMAKERS, MIKE HALPIN, LOREN JACOBS, MICHAEL J. MEYER, FRANK VAN BILSEN, MATT GOODMAN, ERIC BARRETT, ERIC WOOD, BLAKE SAMUELS

Title: LONG LIFE HIGH TEMPERATURE PROCESS CHAMBER

Assignment: 1

Reel/Frame: 010881/0362   **Received:** 07/14/2000   **Recorded:** 06/13/2000   **Mailed:** 08/22/2000   **Pages:** 15

Conveyance: CHANGE OF NAME (SEE DOCUMENT FOR DETAILS).

Assignor: ADVANCED SEMICONDUCTOR MATERIALS AMERICA, INC.   **Exec Dt:** 12/12/1997

Assignee: ASM AMERICA, INC.
3440 EAST UNIVERSITY DRIVE
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Assignment: 2

Reel/Frame: 009701/0741   **Received:** 01/21/1999   **Recorded:** 01/20/1999   **Mailed:** 04/17/1999   **Pages:** 8

Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

Assignors:

WENGERT, JOHN F.	**Exec Dt:** 11/19/1998
RAAIJMAKER, IVO	**Exec Dt:** 10/23/1998
HALPIN, MIKE	**Exec Dt:** 11/16/1998
JACOBS, LOREN	**Exec Dt:** 10/29/1998
MEYER, MICHAEL J.	**Exec Dt:** 10/29/1998
VAN BILSEN, FRANK	**Exec Dt:** 10/29/1998
GOODMAN, MATT	**Exec Dt:** 10/29/1998
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WOOD, ERIC	**Exec Dt:** 10/29/1998
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Search Results as of: 1/9/2003 1:57:36 P.M.

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Patent Assignment Abstract of Title

Total Assignments: 1

Application #: 09439833 **Filing Dt:** 11/12/1999   **Patent #:** 6342691 **Issue Dt:** 01/29/2002

PCT #: NONE   **Publication #:** NONE   **Pub Dt:**

Inventors: KRISTIAN E. JOHNSGARD, JEAN-FRANCOIS DAVIET, JAMES A. GIVENS, STEPHEN E. SAVAS, BRAD S. MATTSON, ASHUR J. ATANOS

Title: APPARATUS AND METHOD FOR THERMAL PROCESSING OF SEMICONDUCTOR SUBSTRATES

Assignment: 1

Reel/Frame: 010709/0817 **Received:** 04/24/2000   **Recorded:** 04/14/2000   **Mailed:** 06/20/2000   **Pages:** 2

Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

Assignors:	JOHNSGARD, KRISTIAN E.	**Exec Dt:** 04/12/2000
	DAVIET, JEAN-FRANCOIS	**Exec Dt:** 03/24/2000
	GIVENS, JAMES A.	**Exec Dt:** 04/10/2000
	SAVAS, STEPHEN E.	**Exec Dt:** 03/06/2000
	MATTSON, BRAD S.	**Exec Dt:** 03/31/2000
	ATANOS, ASHUR J.	**Exec Dt:** 04/12/2000

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Search Results as of: 1/9/2003 11:36:26 A.M.

If you have any comments or questions concerning the data displayed, contact OPR / Assignments at 703-308-9723
Web interface last modified: Oct. 5, 2002

Patent Assignment Abstract of Title

Total Assignments: 1

Application #: 09828550 **Filing Dt:** 04/06/2001   **Patent #:** NONE   **Issue Dt:**

       PCT #: NONE   **Publication #:** 20020011211   **Pub Dt:** 01/31/2002

     Inventor: Michael W. Halpin

         Title: Barrier coating for vitreous materials

Assignment: 1

  Reel/Frame: 011687/0225 **Received:** 04/20/2001   **Recorded:** 04/06/2001   **Mailed:** 07/02/2001   **Pages:** 2

    Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

      Assignor: HALPIN, MICHAEL W.   **Exec Dt:** 04/06/2001

      Assignee: ASM AMERICA, INC.
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Correspondent: KNOBBE, MARTENS, OLSON & BEAR, LLP
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Search Results as of: 1/9/2003 11:35:46 A.M.

L Number	Hits	Search Text	DB	Time stamp
1	2	6342691.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 10:46
8	32	((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 10:54
15	1	(quartz or 'SiO.sub.2') and ("silicon nitride" or 'Si.sub.3 N.sub.4') and (((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:04
22	0	6120640.pn. and sputter$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:43
29	0	6120640.pn. and sputt$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:45
36	0	5910221.pn. and sputt$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:44
43	2	6120640.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:51
50	3349	(Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:14
57	1904	((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:59
64	475	(((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect$3) and (thickness same (".mu.m" or angstrom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:15
71	33	((((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect$3) and (thickness same (".mu.m" or angstrom))) and corrosiv$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:00
78	442	((((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect$3) and (thickness same (".mu.m" or angstrom))) not (((((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect$3) and (thickness same (".mu.m" or angstrom))) and corrosiv$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:04
85	181	(((((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect$3) and (thickness same (".mu.m" or angstrom))) not (((((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and protect$3) and (thickness same (".mu.m" or angstrom))) and corrosiv$5)) and (chamber or reactor or vessel or tank)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:15

92	35	((Sputter$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom)) and lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:13
99	291	(Sputter$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:18
106	53	((Sputter$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:15
113	20	(((Sputter$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))) and (chamber or reactor or vessel or tank)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
120	271	((Sputter$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) not (((((Sputter$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))) and (chamber or reactor or vessel or tank))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
127	9	(((Sputter$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) not (((((Sputter$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same (".mu.m" or angstrom))) and (chamber or reactor or vessel or tank))) and lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
134	464	(Sputter$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with (protect$4 or prevent$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:21
141	5	((Sputter$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with (protect$4 or prevent$4)) and (118/$.ccls. or 156/$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
148	1	(Sputter$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
155	43	(Sputter$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with wall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:27
162	2	((Sputter$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with wall) and (118/$.ccls. or 156/$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
169	51	(Sputter$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) and 118/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:28

L Number	Hits	Search Text	DB	Time stamp
1	2	6342691.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 10:46
8	32	((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 10:54
15	1	(quartz or 'SiO.sub.2') and ("silicon nitride" or 'Si.sub.3 N.sub.4') and (((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 11:04